

SiPM e ALCOR

2 settembre 2021 -- incontro EIC_NET con i referee INFN

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SiPM R&D program

- **born within the forward RICH proposal for EIC**
 - proof of feasibility of SiPM for Cherenkov application at colliders, this requires
 - single-photon counting capabilities (SiPM can do it)
 - reasonable dark-count rates (low-temperature operation, time resolution)
 - radiation tolerance (small SPAD cells, high-temperature annealing)
 - SiPM readout with dedicated readout electronics
 - ALCOR front-end ASIC (Torino)
 - streaming (aka continuous) readout DAQ
- **two main phases in 2021**
 - characterisation of the sensors before and after irradiation
 - use of the sensors (with/without irradiation) in dRICH prototype at test beam
- **can have direct applications in multiple cases, i.e.**
 - other EIC detectors looking for B-tolerant photon counters
 - the Aerogel-RICH proposal for ALICE3

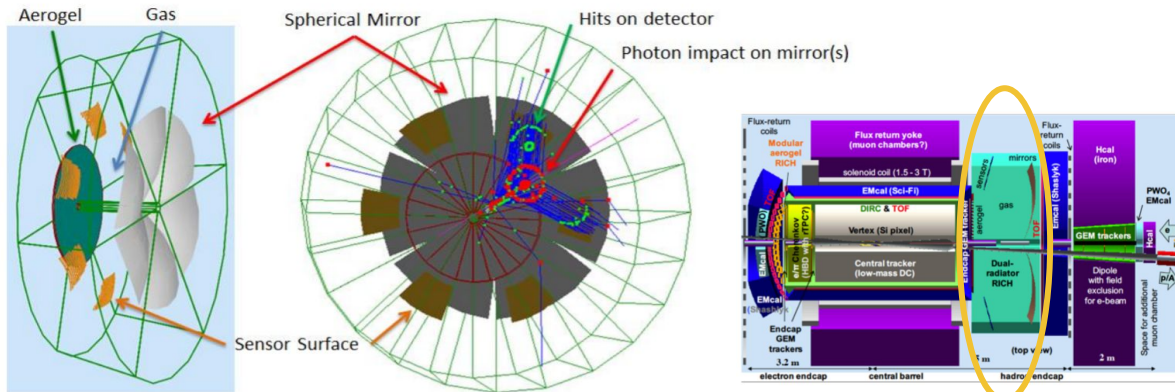
**this R&D is
100% synergic
with ALICE3**

dRICH proposal for forward PID

- **dual-radiator RICH (dRICH)**

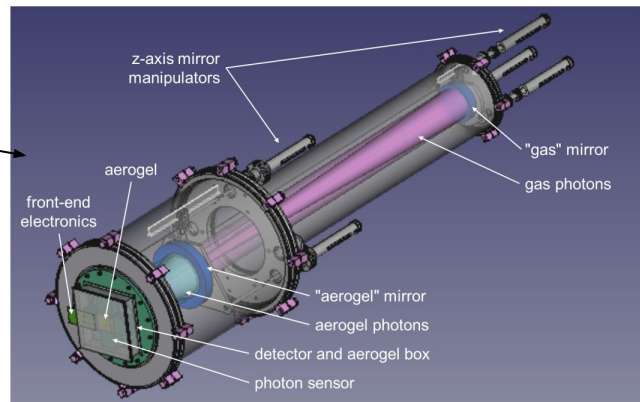
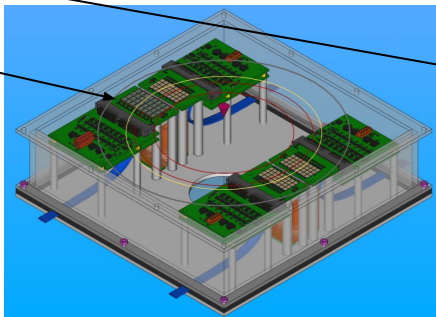
- aerogel ($n \sim 1.02$) + gas ($n \sim 1.0008$)
- for PID in the hadronic endcap
 - $3 < p < 50$ GeV/c
 - $1.5 < \eta < 3.5$
- 6 sectors x 0.5 m²/sector photosensors
 - ~ 1 T magnetic field
 - sensors out of acceptance

explore SiPM readout option

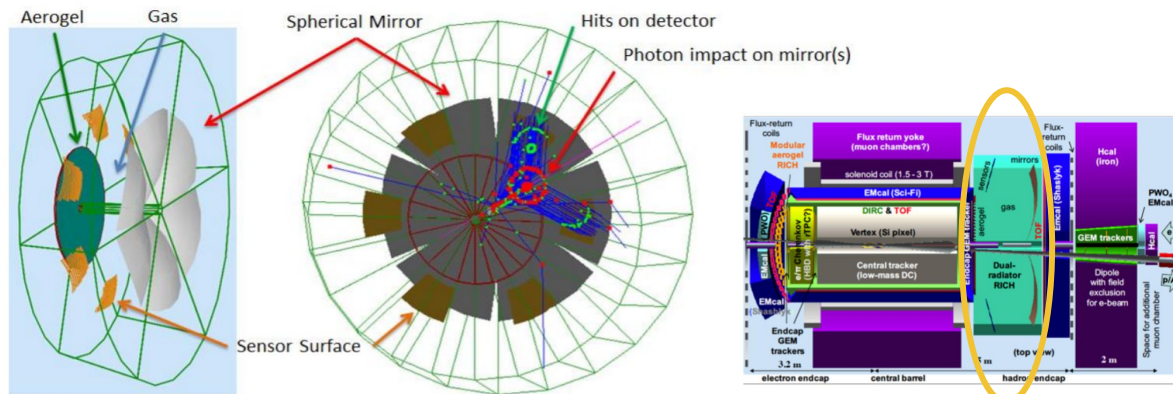


- **realisation of dRICH prototype, test beam in 2021**

- design of electronics boards
- SiPM studies
 - irradiation tests (@ Trento)
 - annealing at high T $\sim 170^\circ$
 - operation at low T $\sim -40^\circ$
- DAQ for front-end readout
 - front-end based on ALCOR



dRICH proposal for forward PID



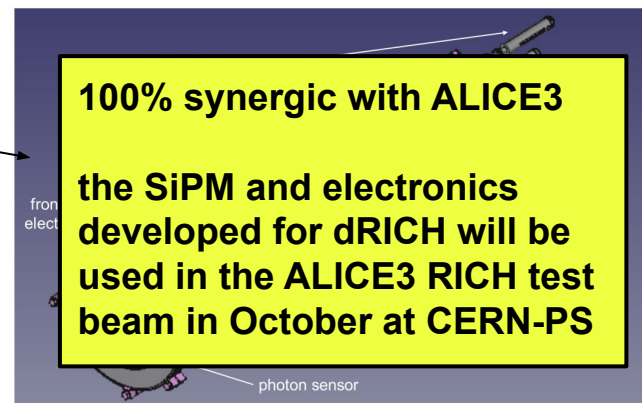
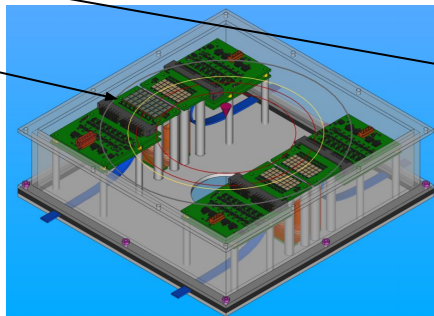
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explore SiPM readout option

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Electronics equipment

acquisition of commercial and prototype (FBK) SiPM sensors
design and production of dedicated electronics boards

- **SiPM carrier boards (BO)**
 - host SiPM matrix: designed with irradiation, annealing and testbeam in mind
 - one form factor, different layout for different SiPM family
- **SiPM adapter boards (FE)**
 - couples the SiPM carrier board with readout system (oscilloscope, ALCOR)
 - IV-base adapter (for SiPM IV and DCR characterisation)
 - mini-adapter (for ALCOR-TEST board)
 - adapter-CA (for ALCOR-FE board)
- **ALCOR FrontEnd board (TO)**
 - hosts ALCOR frontend ASIC
- **FireFly breakout board (ARCADIA)**
 - links ALCOR I/O to FPGA
 - ALCOR configuration and readout

the list does not stop here, these are the main equipment boards

Commercial SiPM sensors

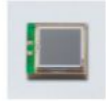
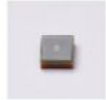
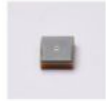
board	sensor	uCell (μm)	V_{bd} (V)	PDE (%)	DCR (kHz/mm ²)	window	notes
HAMA1	S13360 3050VS	50	53	40	55	silicone	legacy model Calvi et. al
	S13360 3025VS	25	53	25	44	silicone	legacy model smaller SPAD
HAMA2	S14160 3050HS	50	38	50		silicone	newer model lower V_{bd}
	S14160 3015PS	15	38	32	78	silicone	smaller SPADs radiation hardness
SENSL	MICROFJ 30035	35	24.5	38	50	glass	different producer and lower V_{bd}
	MICROFJ 30020	20	24.5	30	50	glass	the smaller SPAD version
BCOM	AFBR S4N33C013	30	27	43	111	glass	commercially available FBK-NUVHD

PHOTON IS OUR BUSINESS
HAMAMATSU



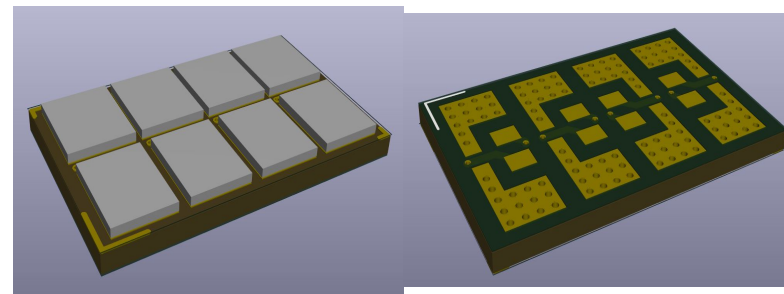
ON Semiconductor®

 BROADCOM



and FBK prototype sensors wire bonded on custom mini-tiles

**FBK has developed for us custom
mini-tiles hosting 2x4 prototypes each**



FBK
FONDAZIONE
BRUNO KESSLER

NUV-HD-RH

2

3.95 mm

3.10 mm

Active area
X x Y = 3.0 x 3.1 mm

NUV-HD-RH

Technology under development
optimized for radiation hardness in
HEP experiments

- Cell pitch 15 μm with high fill factor
- Fast recovery time – reduced cell occupancy
Tau recharge < 15 ns
- Primary DCR @ +24°C ~ 40 kHz/mm²
- Correlated noise 10% @ 6 V

IRIS
INTEGRATED RADIATION
AND IMAGE SENSORS

October 5, 2020 FBK - Confidential

FBK
FONDAZIONE
BRUNO KESSLER

NUV-HD-CHK

4

3.36mm x 3.86mm

Active area
X x Y = 3.2 x 3.1 mm²

NUV-HD big cells

Technology similar to NUV-HD-Cryo
Optimized for single photon timing

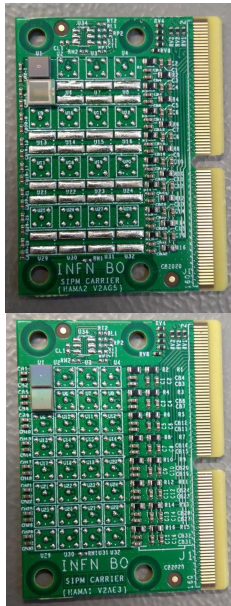
- Cell pitch 40 μm
- High PDE > 55%
- Primary DCR @ +24°C ~ 50 kHz/mm²
- Correlated noise 35% @ 6 V

IRIS
INTEGRATED RADIATION
AND IMAGE SENSORS

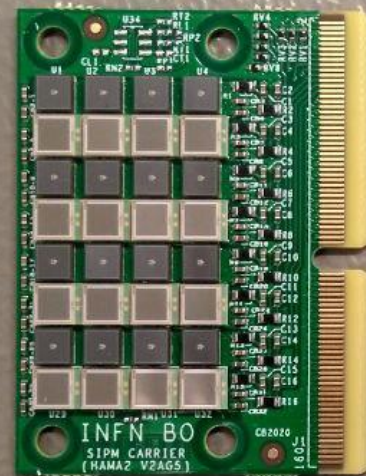
October 5, 2020 FBK - Confidential

Schede SiPM carrier

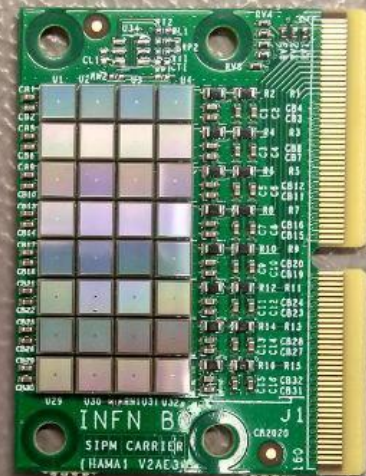
- **SENSL**
 - 2 schede FULL
 - 3 schede LIGHT
- **BCOM**
 - 4 schede FULL
 - 2 schede LIGHT
- **HAMA1**
 - 2 schede FULL
 - 3 schede LIGHT
- **HAMA2**
 - 2 schede FULL
 - 3 schede LIGHT
- **FBK**
 - 4 schede FULL



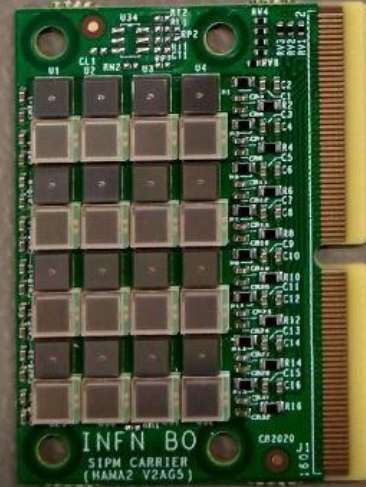
schede LIGHT



HAMA2

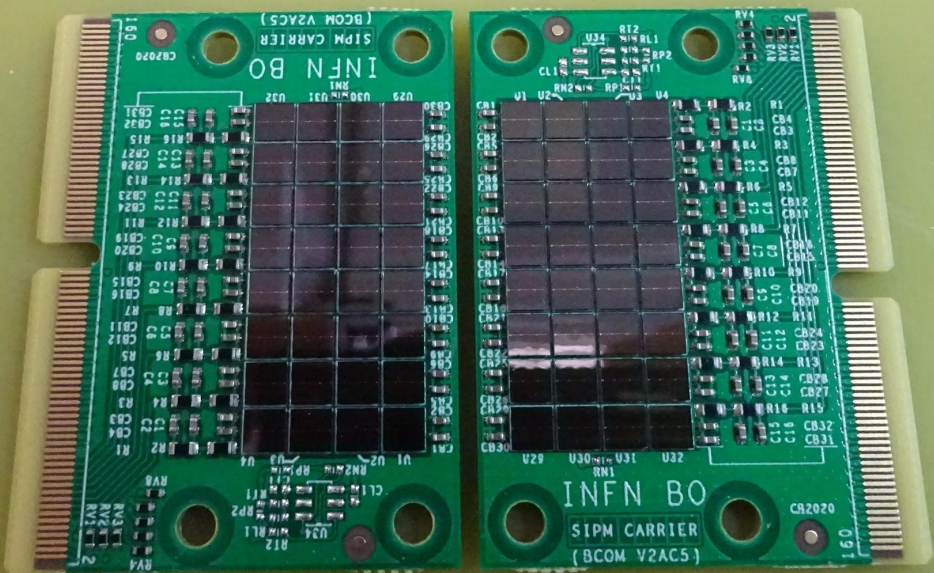


HAMA1



schede FULL

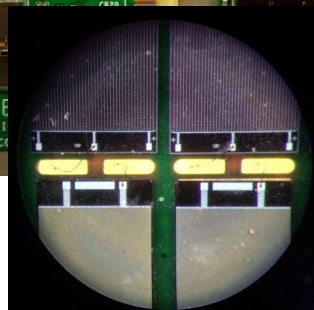
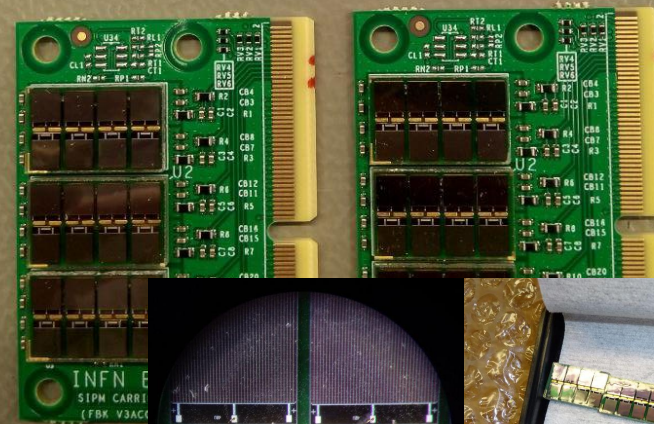




BCOM

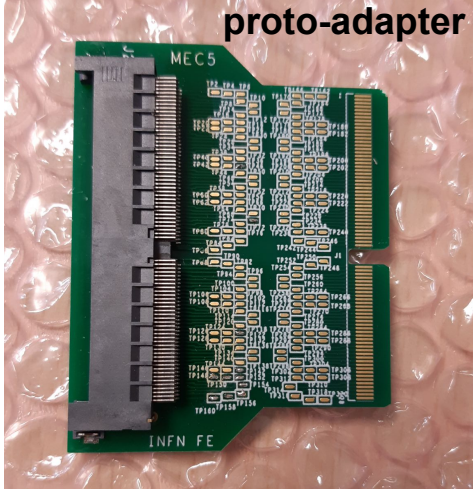


FBK



Schede adapter

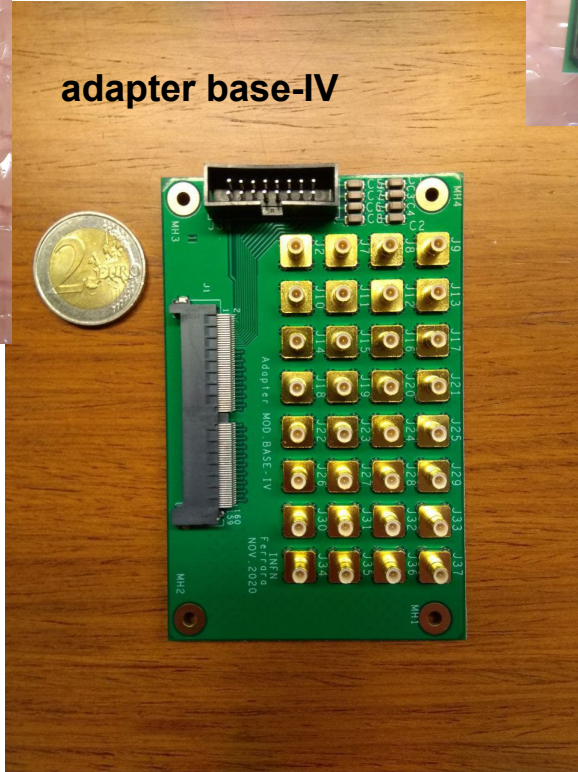
proto-adapter



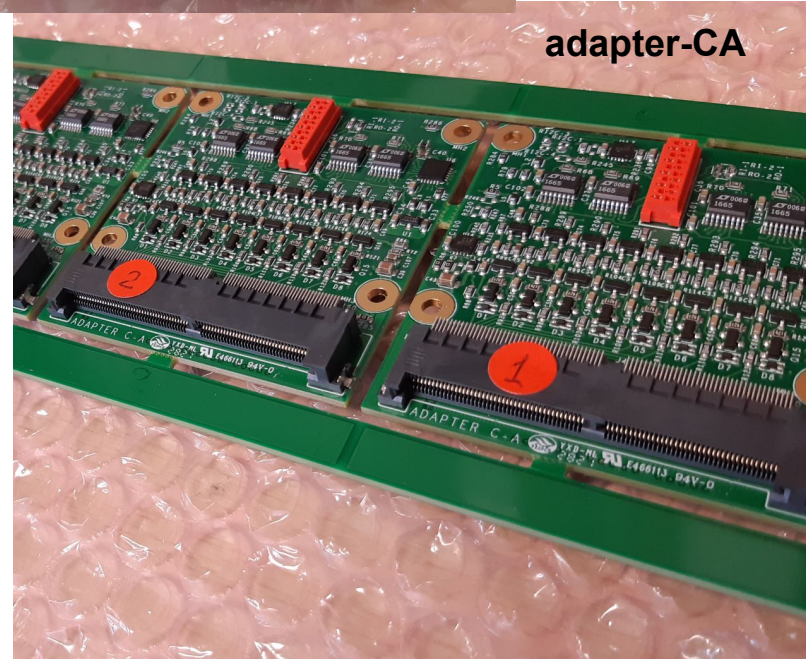
mini-adapter



adapter base-IV



adapter-CA



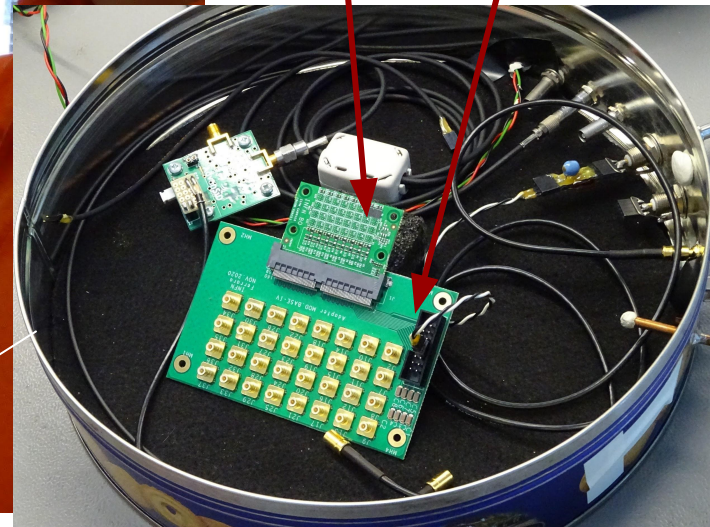


in azienda durante
produzione schede SiPM

segnali dai SiPM !

SiPM carrier LIGHT

SiPM adapter Base-IV



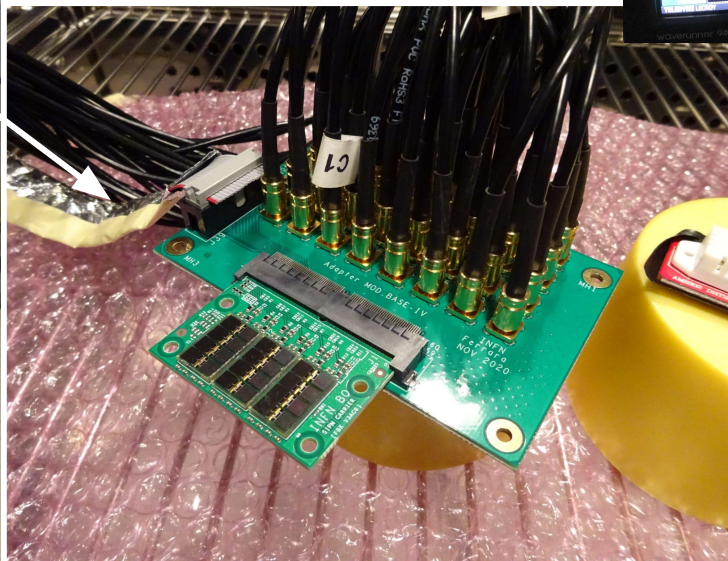
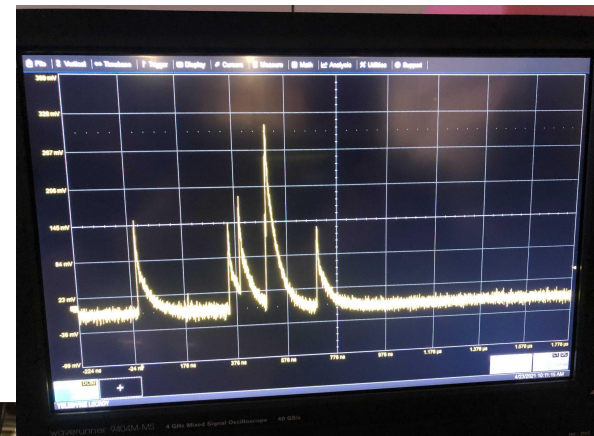
SiPM characterisation @ BO



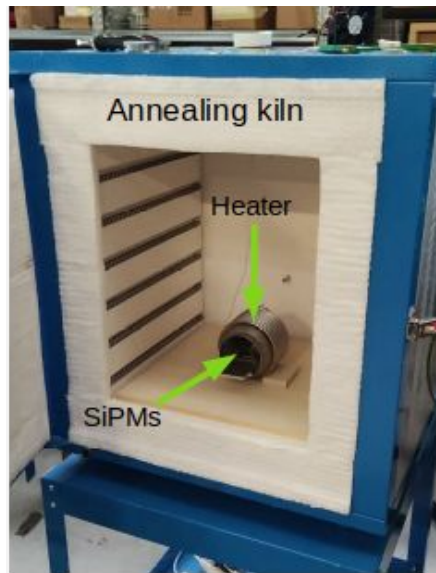
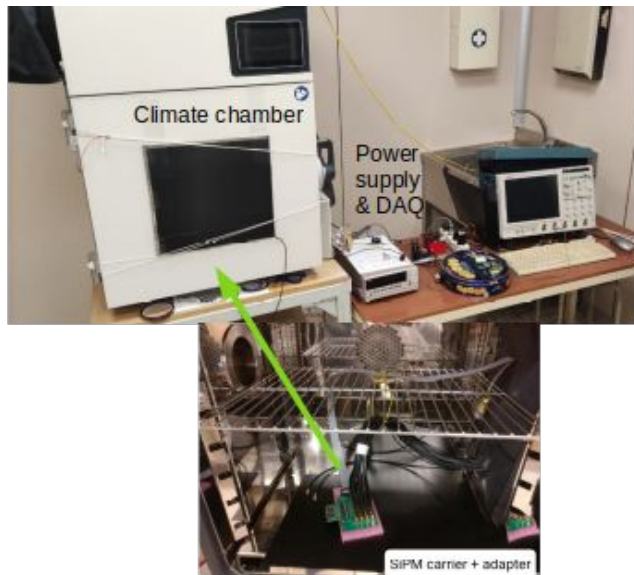
I-V curves and DCR at different temperatures

+20 C -10 C -30 C

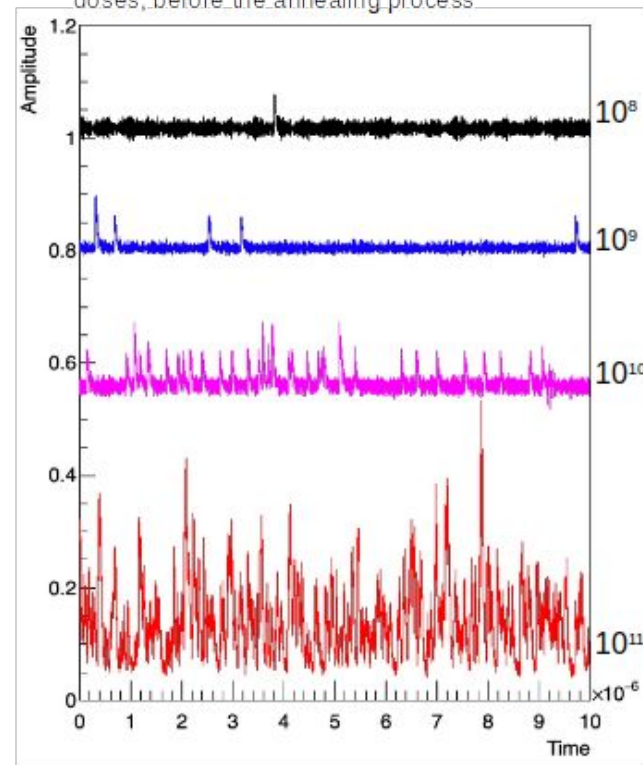
- Memmert climatic chamber
- Keithley source meter
- Keysight power supply
- Cividec amplifier
- Lecroy oscilloscope



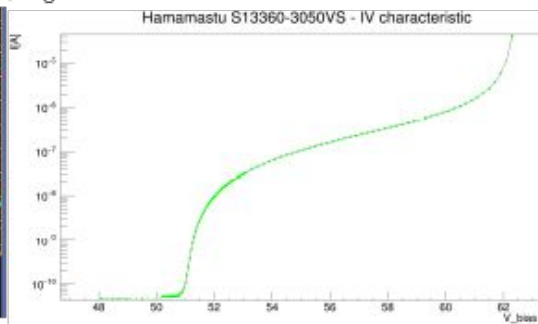
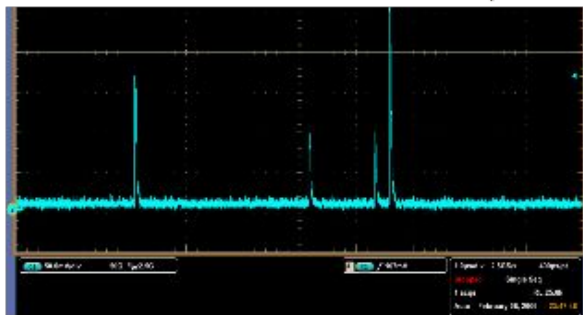
SiPM characterisation @ FE



Signals of SiPMs irradiated with different doses, before the annealing process



Not irradiated SiPMs, room temperature, signal and IV characteristic

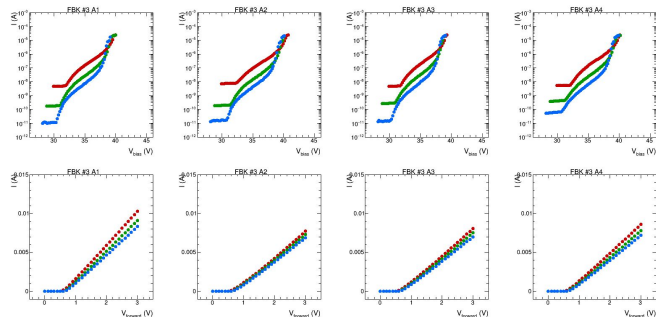


SiPM characterisation

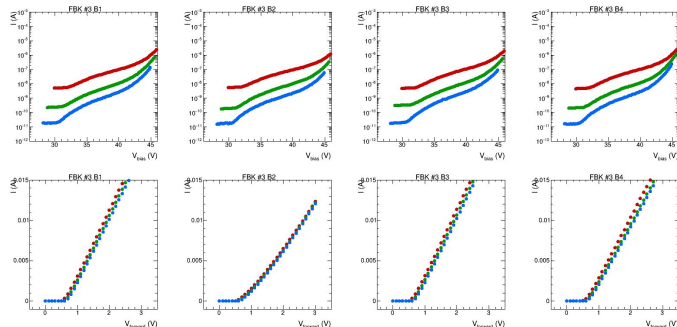
IV characteristics at different T

+20 C
-10 C
-30 C

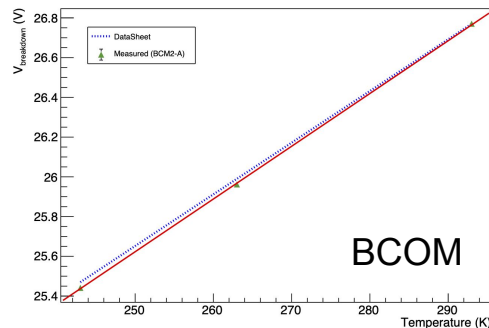
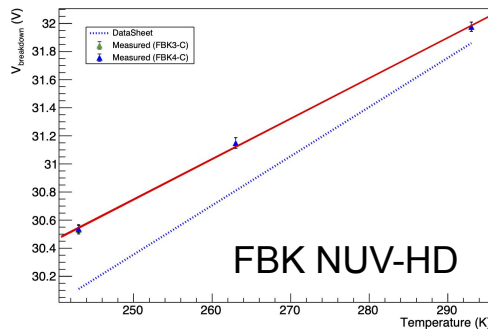
FBK NUV-HD-CHK



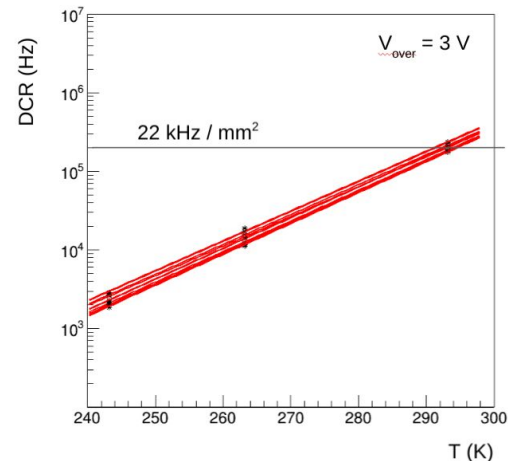
FBK NUV-HD-RH



breakdown voltage vs. temperature



dark count rate vs. temperature



only a little fraction of the large amount of data collected shown

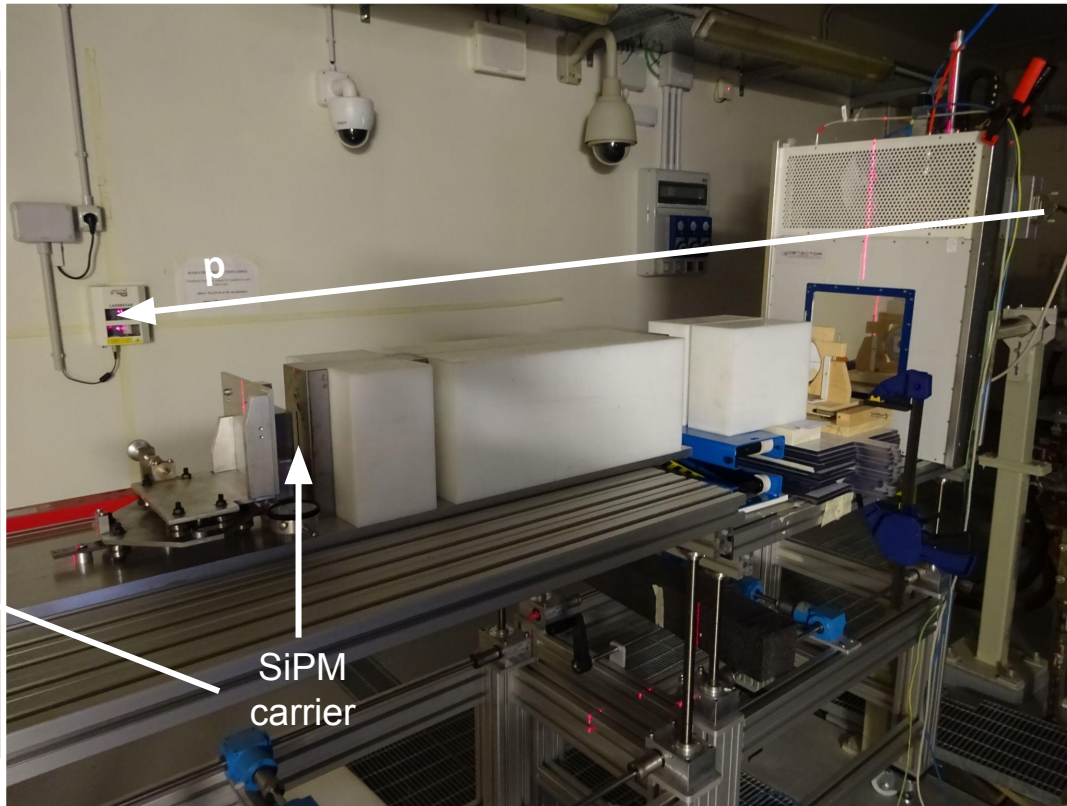
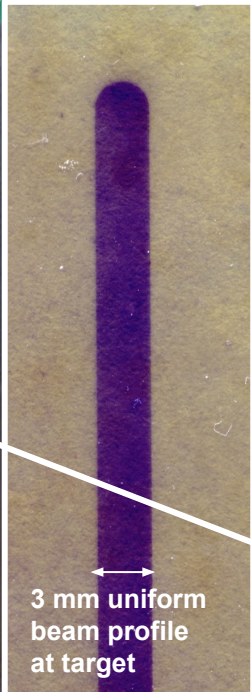
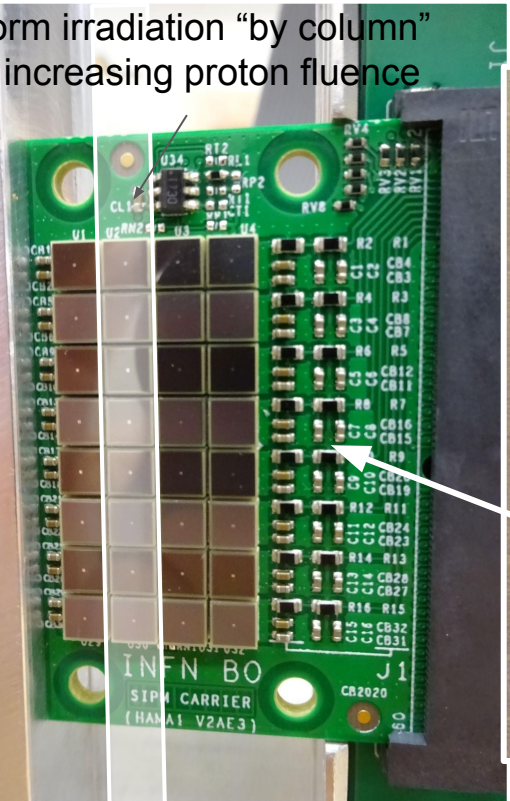
1st irradiation round in May

3x3 mm² SiPM sensors
4x8 “matrix” (carrier board)

multiple types of SiPM: **Hamamatsu** commercial (13360 and 14160)
FBK prototypes (rad.hard and timing optimised)

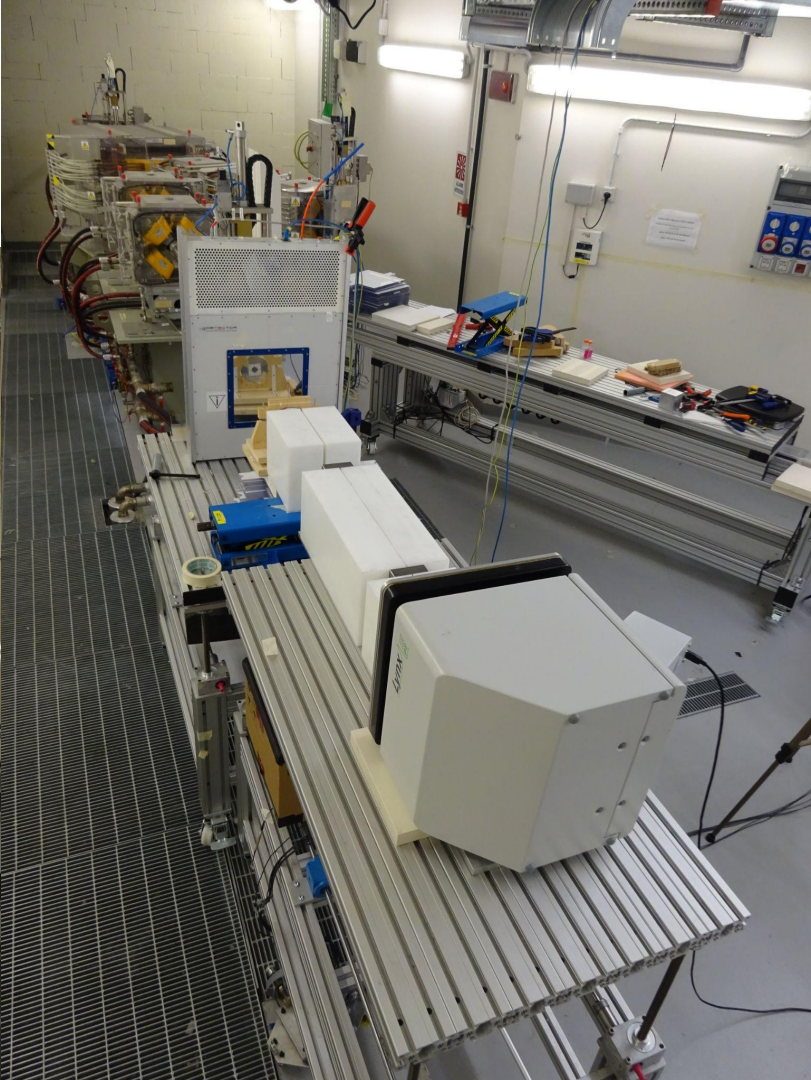
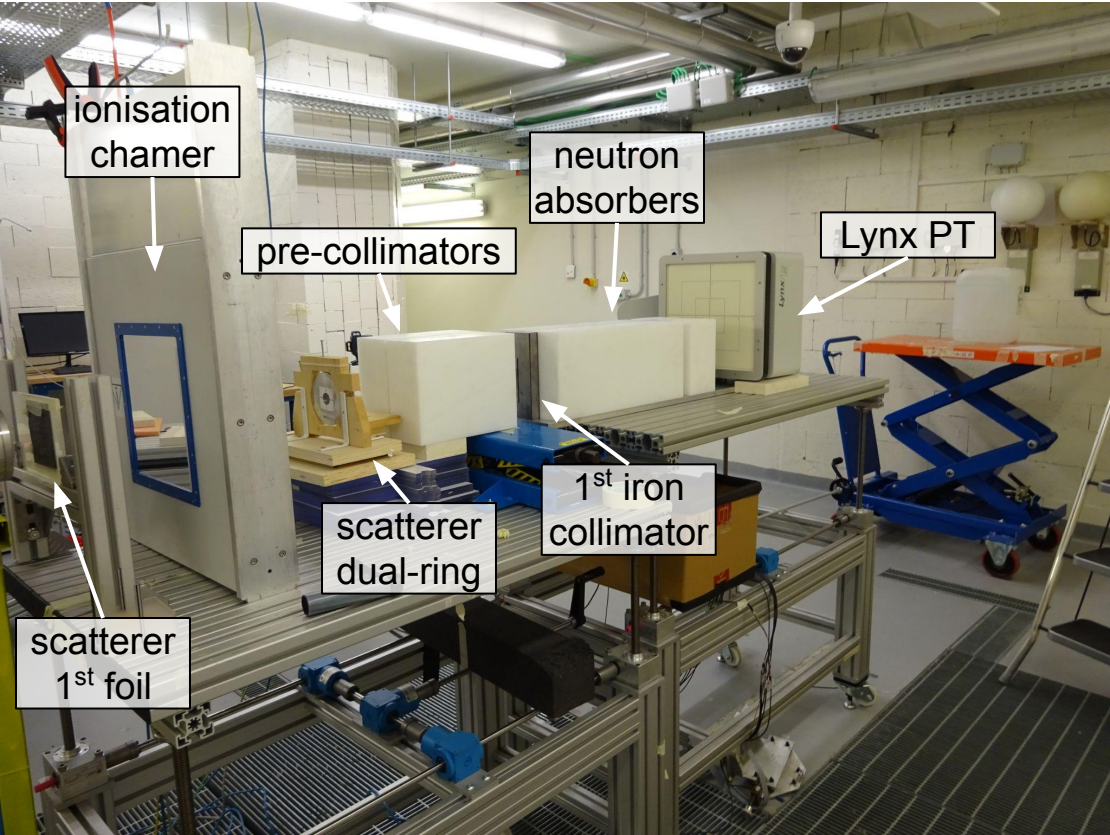
148 MeV protons → scattering system → collimation system → carrier board

uniform irradiation “by column”
with increasing proton fluence



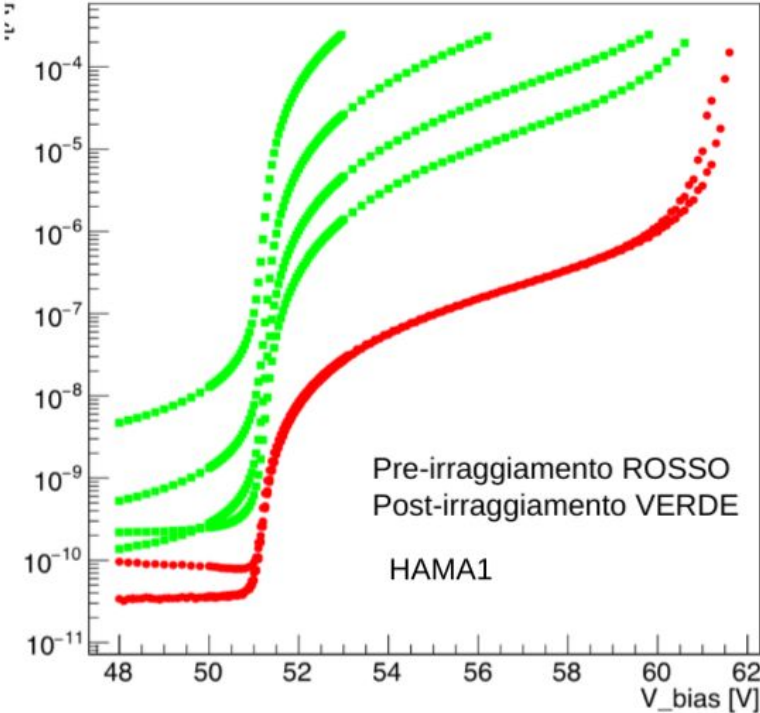
Hamamatsu 13360 carrier board

Collimator setup: intensity calibration

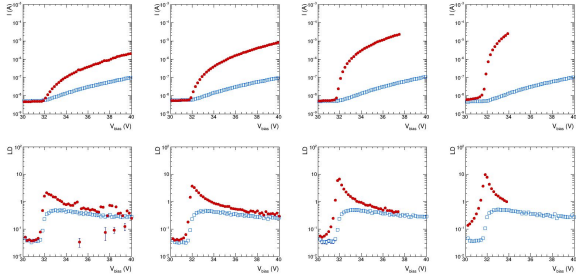


Post-irradiation characterisation

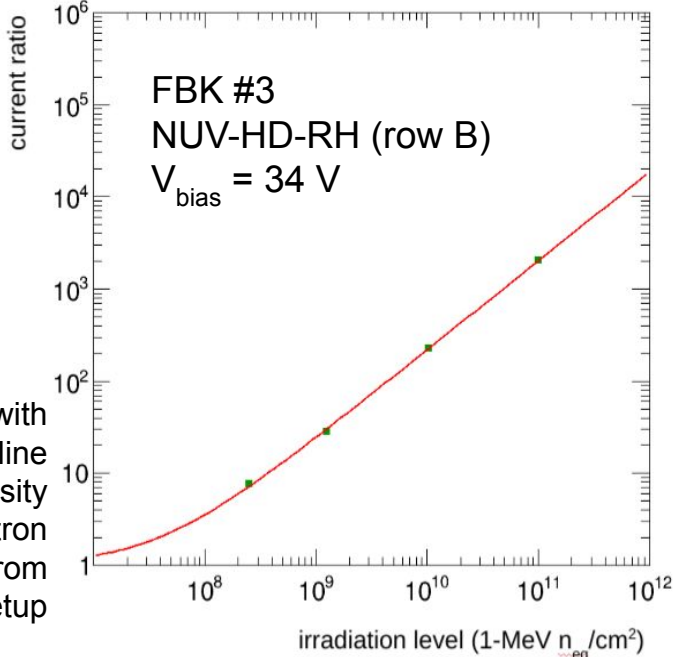
measured also right after irradiation in TIFPA bunker and ~10 days later when TIFPA released the SiPM



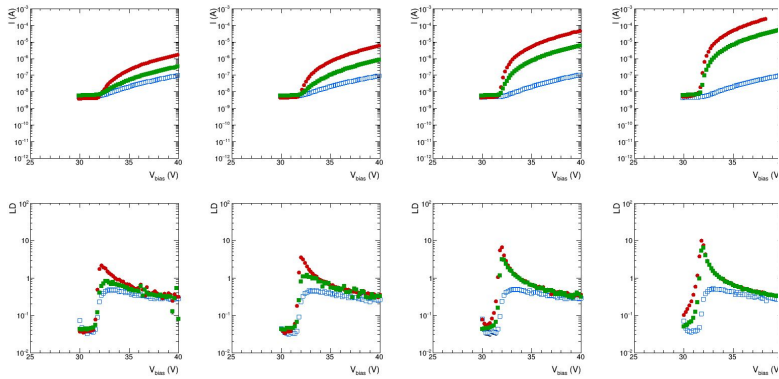
after
before



current increases with irradiation level in line with proton intensity calibration + neutron background from simulations of the setup



FBK characterisation after 1 week of annealing at T = 125 C

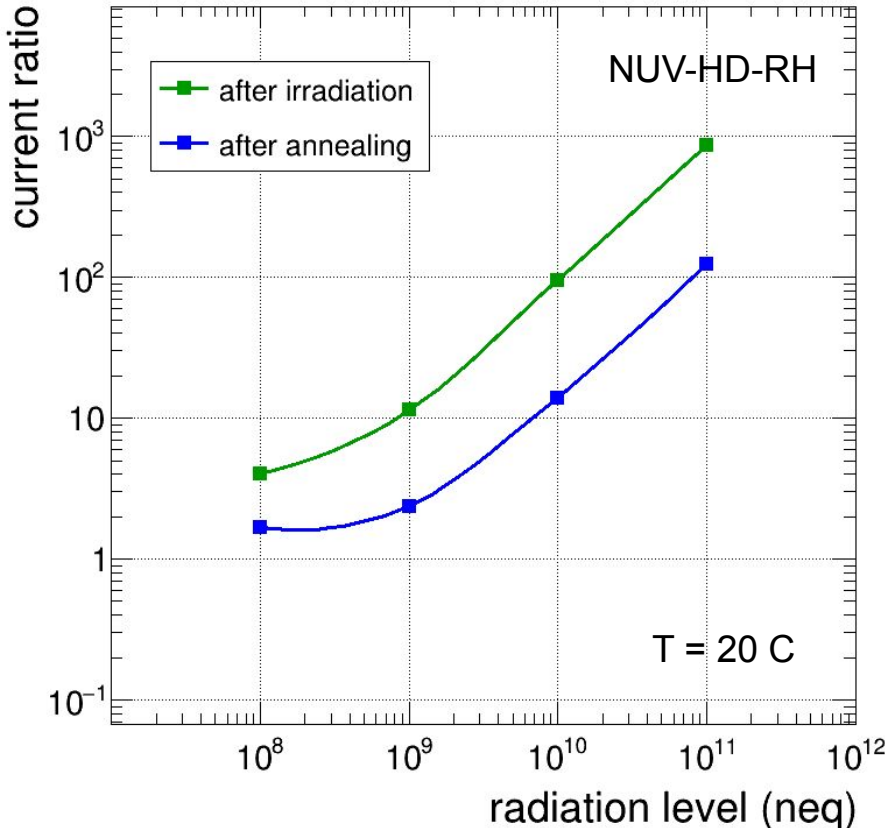


new
irradiated
annealed

annealing reduced dark current by a factor of ~5-10, in line with expectations

SiPM irradiated up to 10^{11} now behave like if they were irradiated by 10^{10}

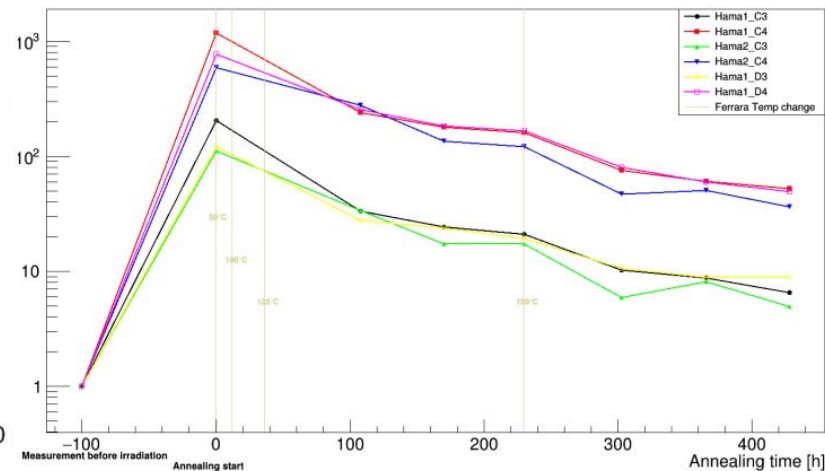
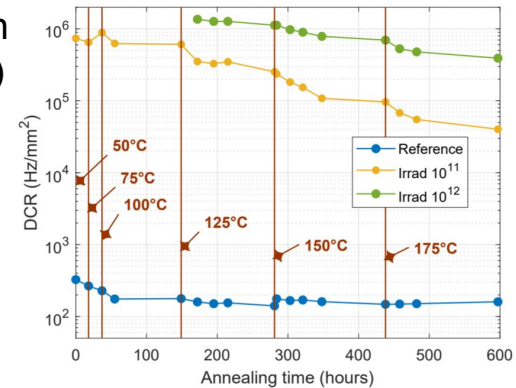
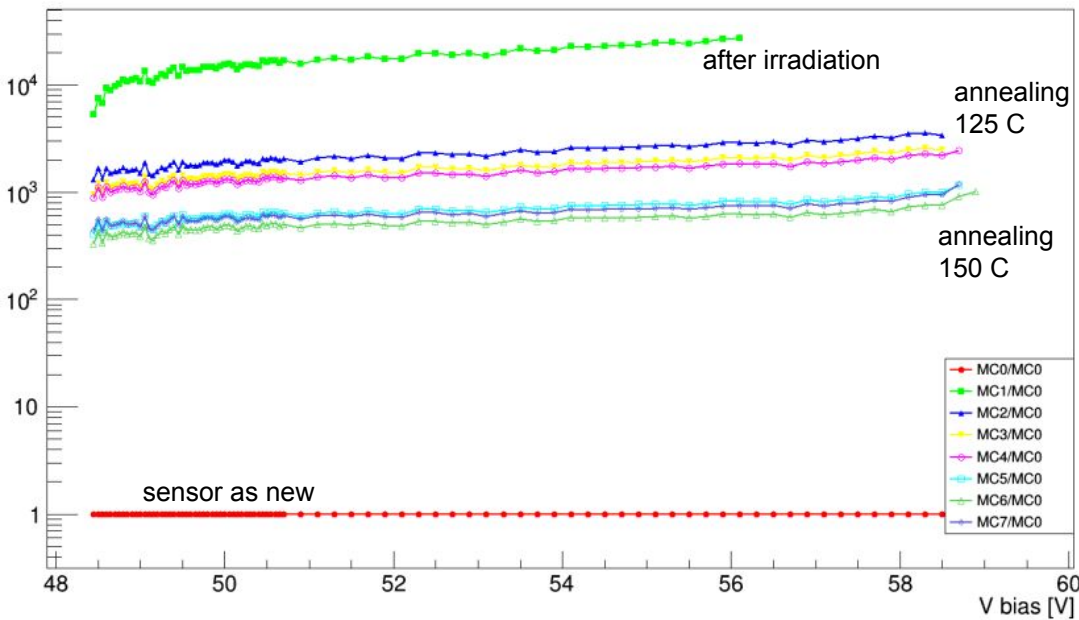
FBK annealing stops at 125 C for the time being
 little issue related to the solder paste used during assembly (T = 138 C) does not allow to reach T = 175
 → needs reworking of the carriers
 → will be done after test beam



Hamamatsu annealing up to $T = 150$ C completed

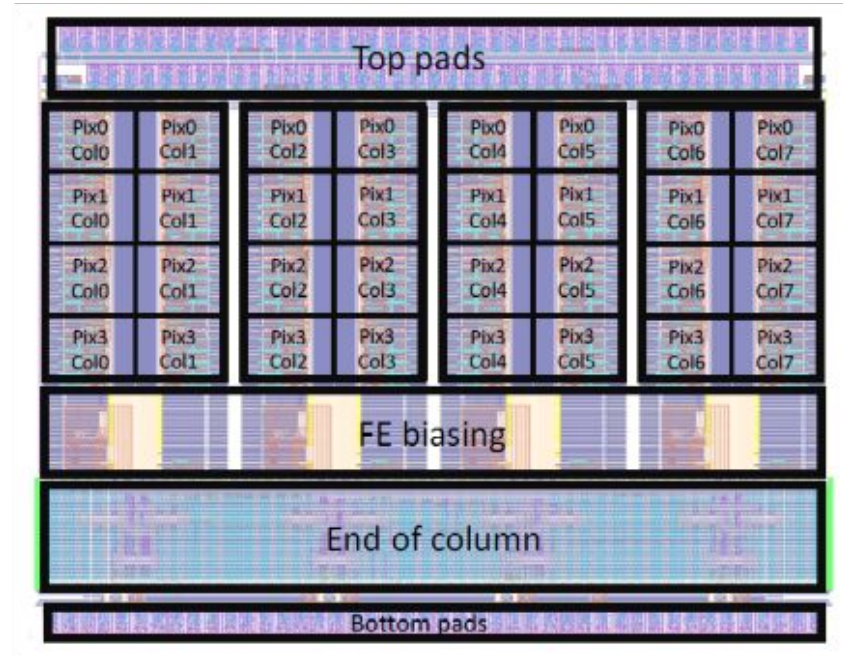
behaviour in line with literature (Calvi et al)

current ratio wrt. before irradiation



ALCOR – A Low Power Chip for Optical sensor Readout

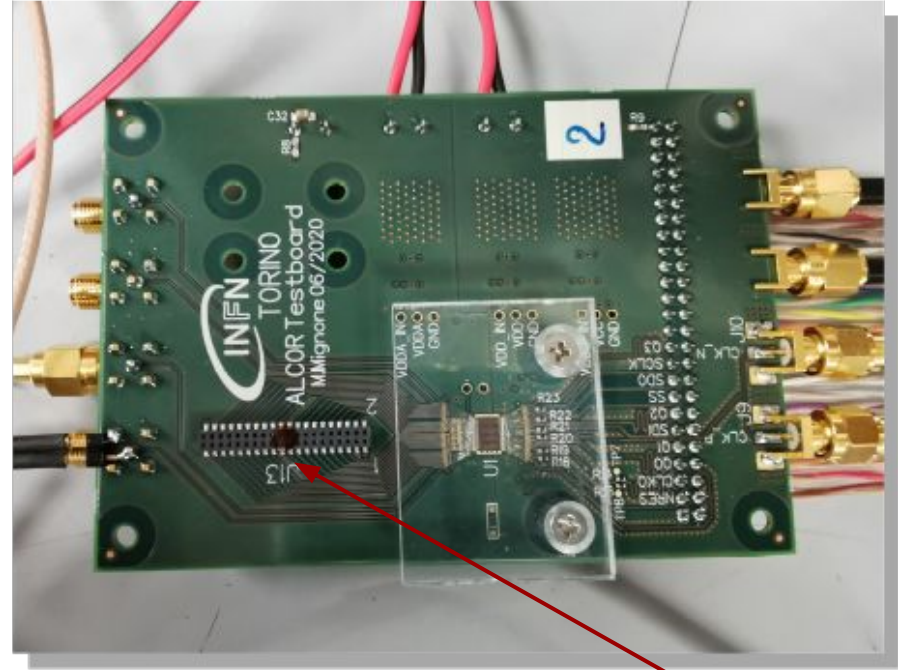
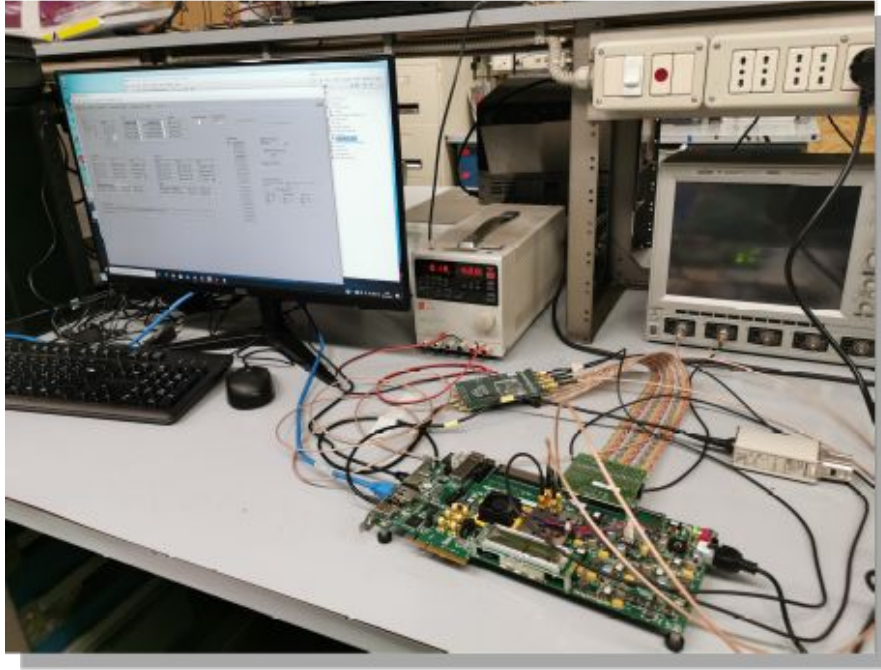
- 32-pixel matrix mixed-signal ASIC
- The chip performs signal amplification and conditioning and event digitization
- Each pixel features:
 - Dual-polarity front-end amplifier with low input impedance (10-20 Ω) and 4 programmable gain settings
 - 2 leading edge discriminators for events selection
 - 4 TDCs based on analogue interpolation: time binning \approx 50ps (@320 MHz clock frequency)
- Single-photon time tagging mode or time and charge measurement (Time-over-Threshold)
- Fully digital output (4 LVDS TX data links)



**developed by TO for Darkside
2022: ALCOR++ optimised for RICH**

ALCOR test-bench setup in Torino

for characterisation of the ALCOR chip with a test board and first look at signal from SiPM carriers

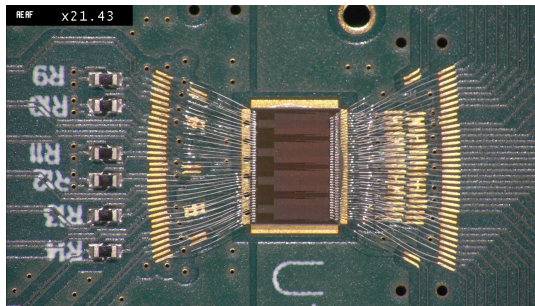


ALCOR test board not designed within EIC_NET R&D
utilised with EIC_NET SiPM boards via dedicated mini-adapter board

connector to mini-adapter board

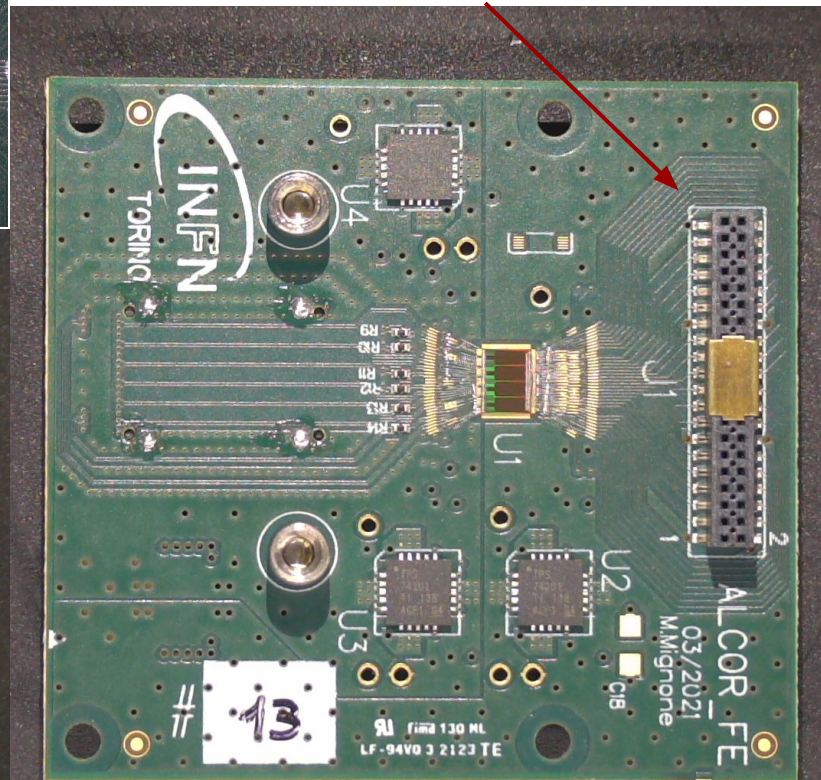
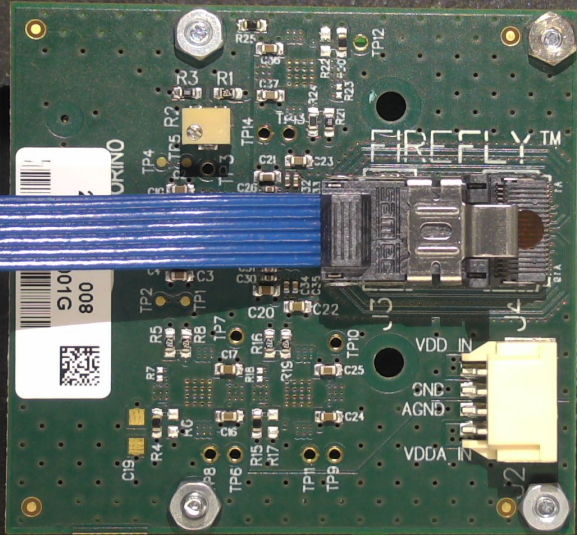
ALCOR – A Low Power Chip for Optical sensor Readout

ALCOR-FE frontend board for testbeam with bonded ALCOR chip and FireFly cable



connector to adapter-CA board

REF x4.39



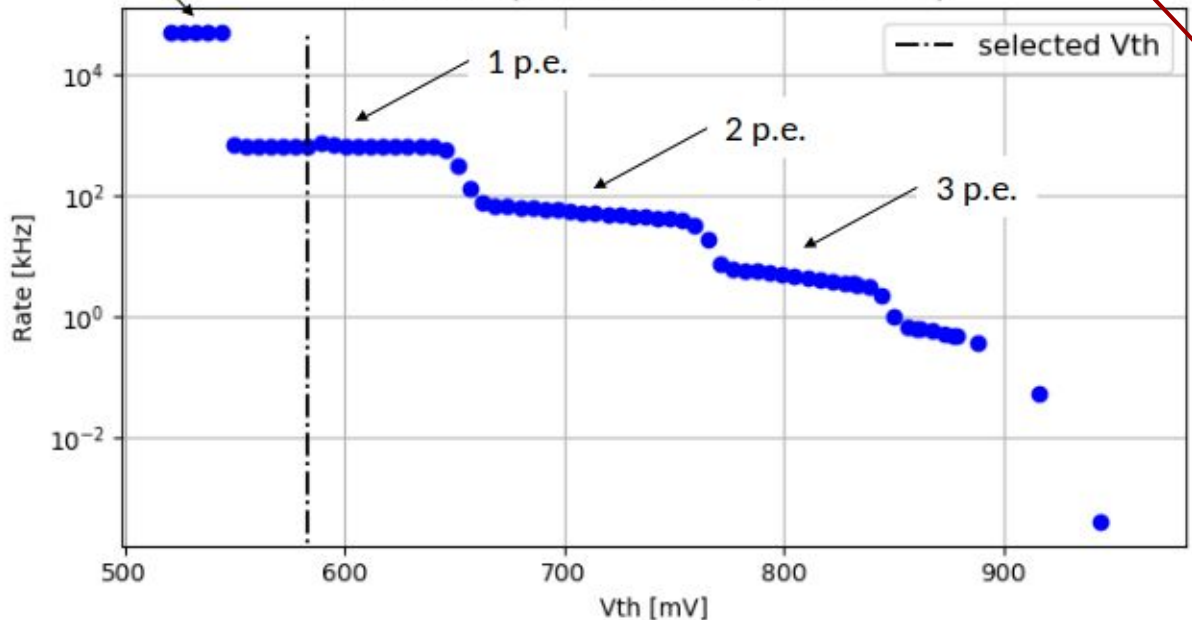
ALCOR threshold scan

final electronics setup during functional tests in Torino

baseline noise

VTH scan (S13360-3050VS, Vbias=56V)

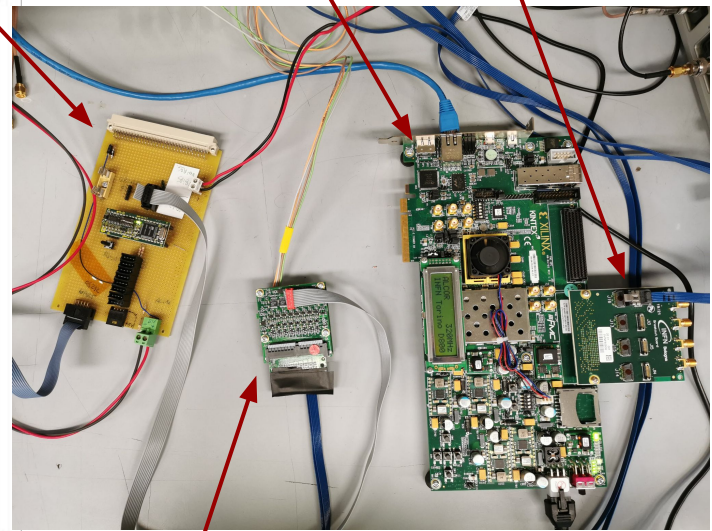
--- selected Vth



SiPM HV controller board

FireFly breakout board

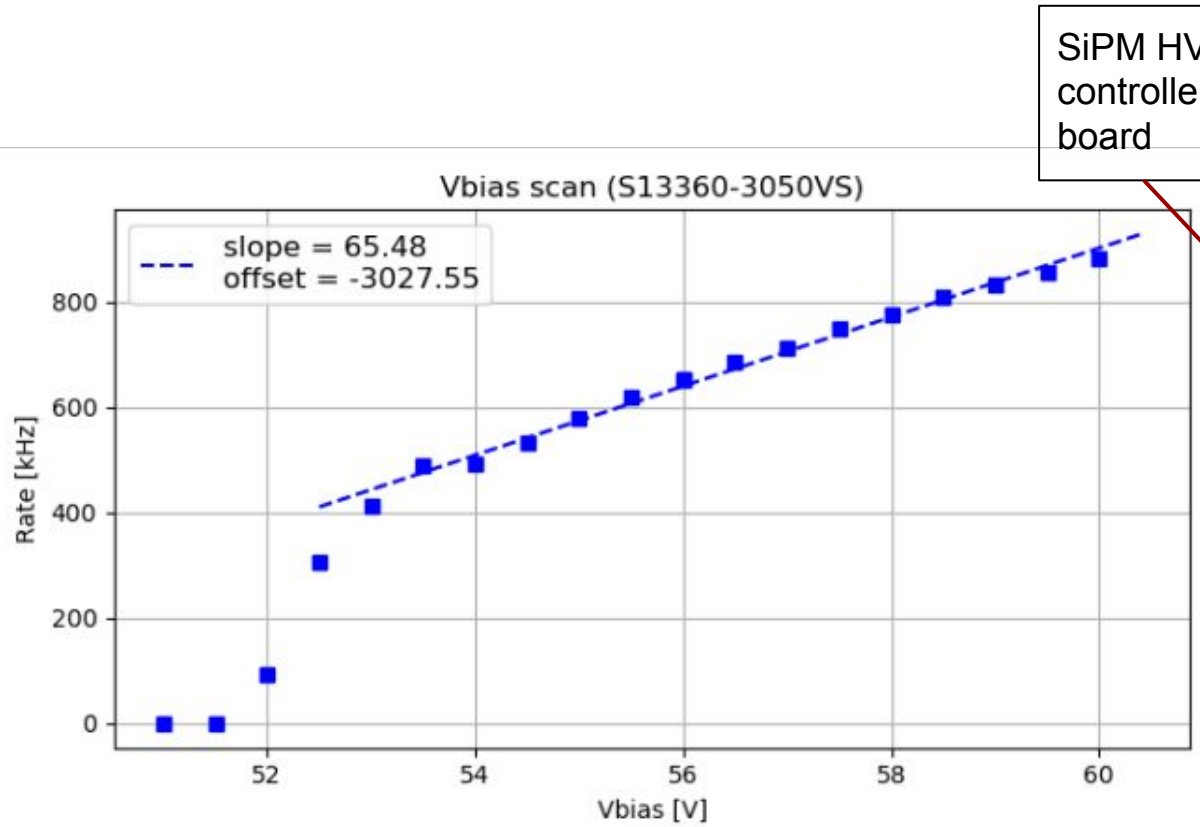
Xilinx FPGA board



SiPM carrier + adapter + ALCOR-FE

SiPM Vbias scan

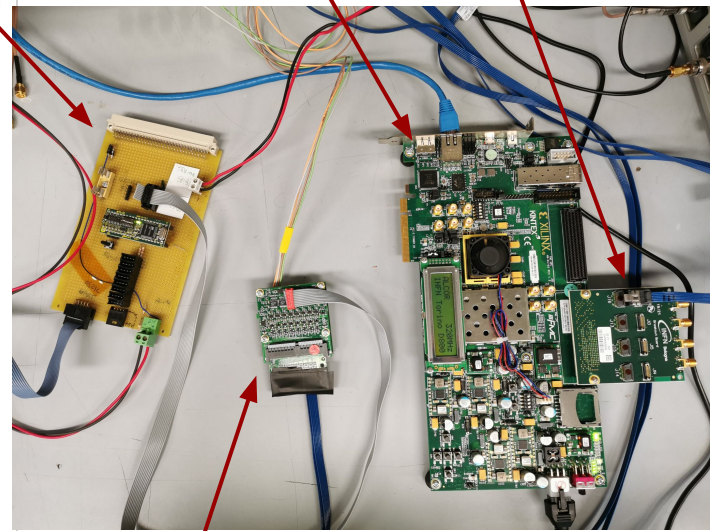
final electronics setup during functional tests in Torino



SiPM HV controller board

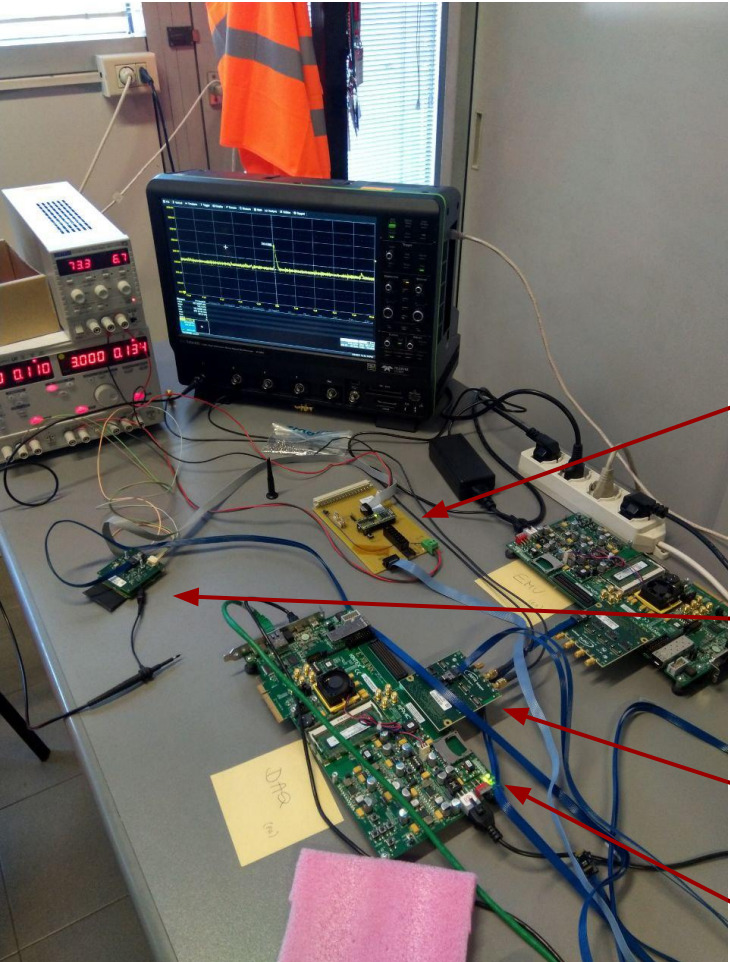
FireFly breakout board

Xilinx FPGA board



SiPM carrier + adapter + ALCOR-FE

DAQ tests for ALCOR readout in Bologna

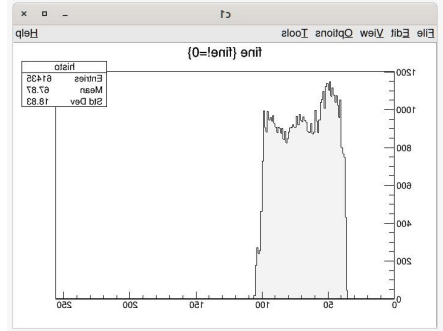
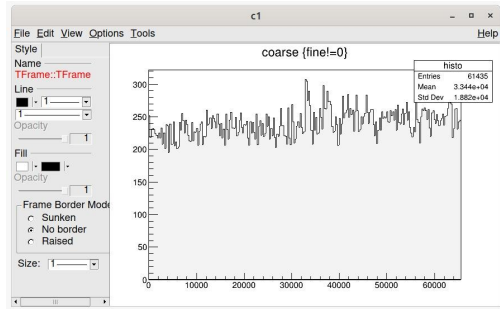


SiPM HV controller board

SiPM carrier + adapter + ALCOR-FE

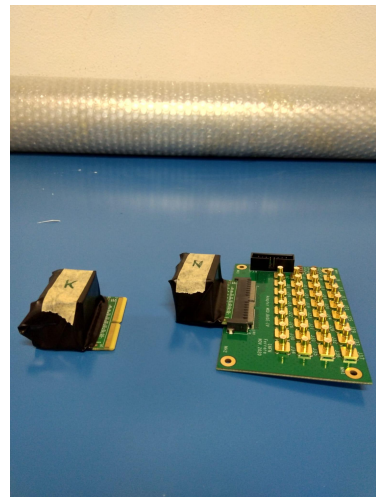
FireFly breakout board

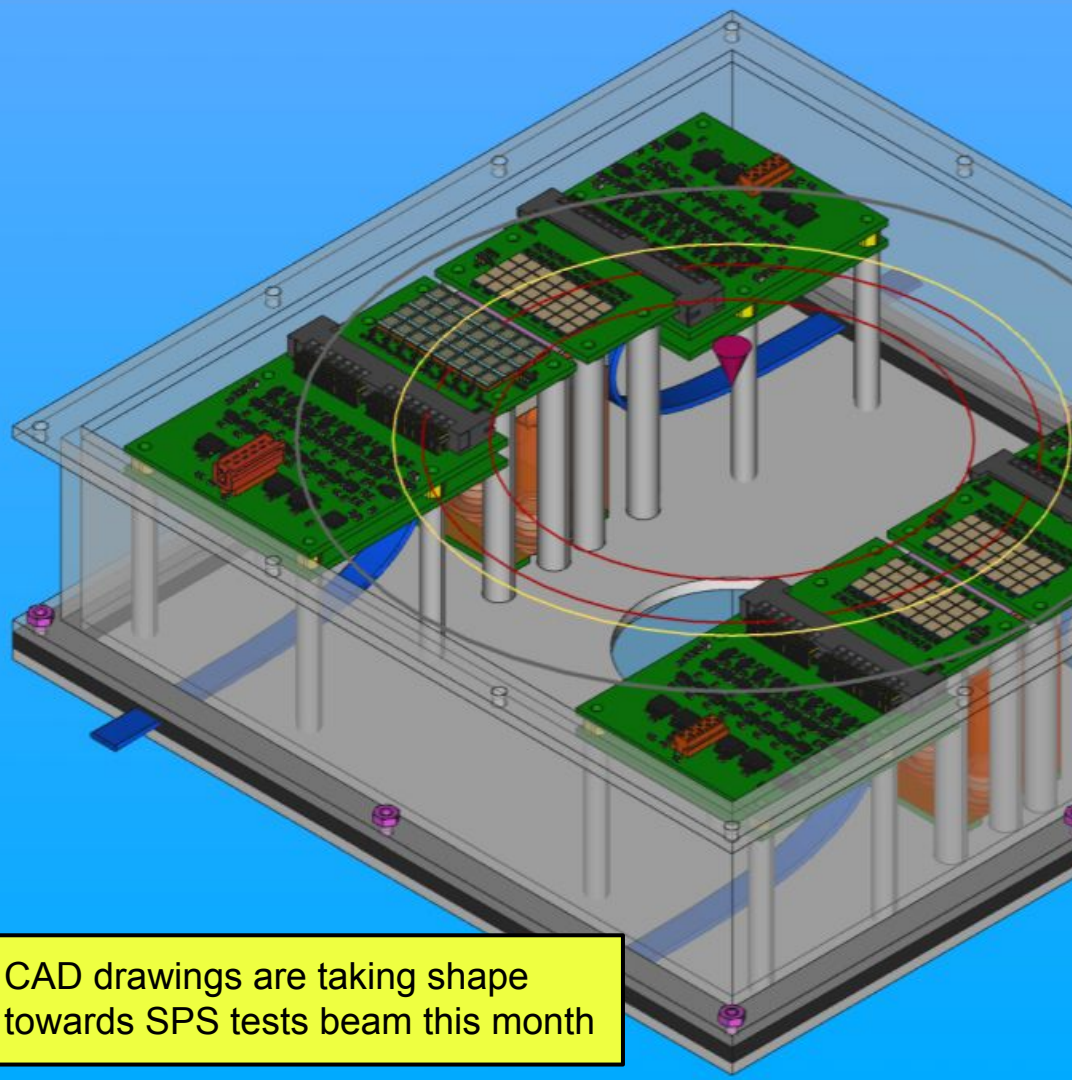
Xilinx FPGA board



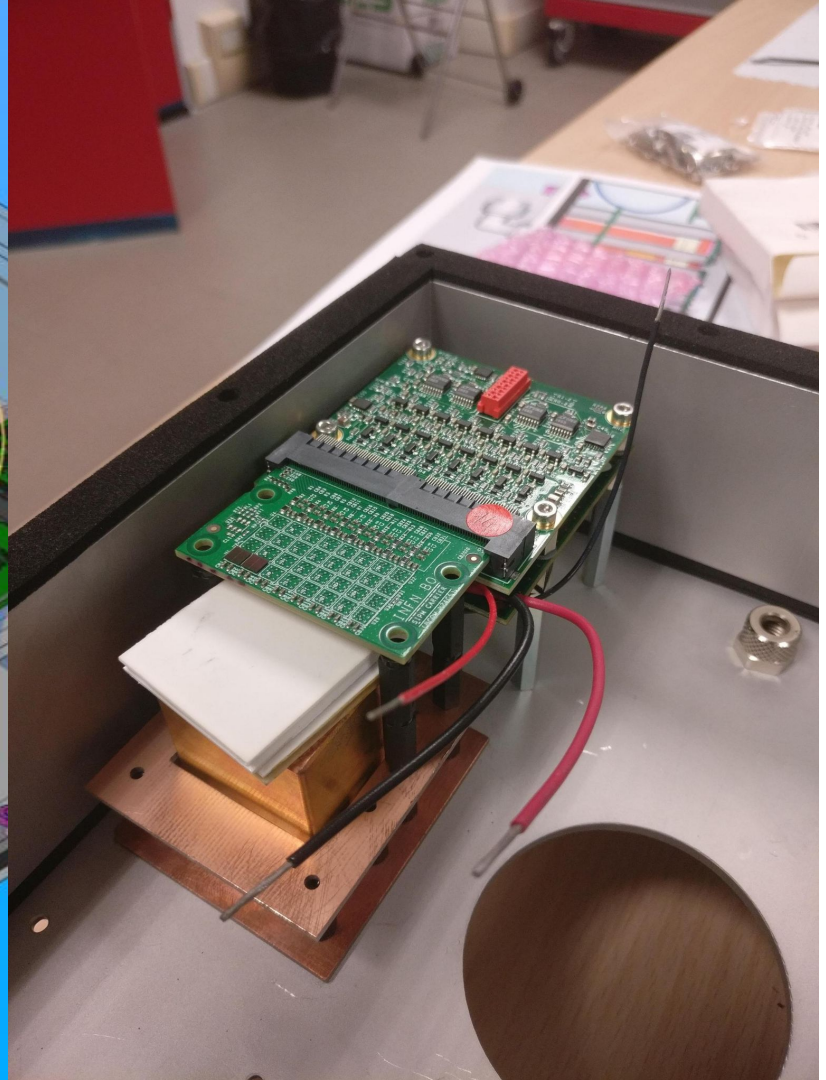
so far only noise rates

soon cosmic rays (with scintillators coupled to SiPM matrices)



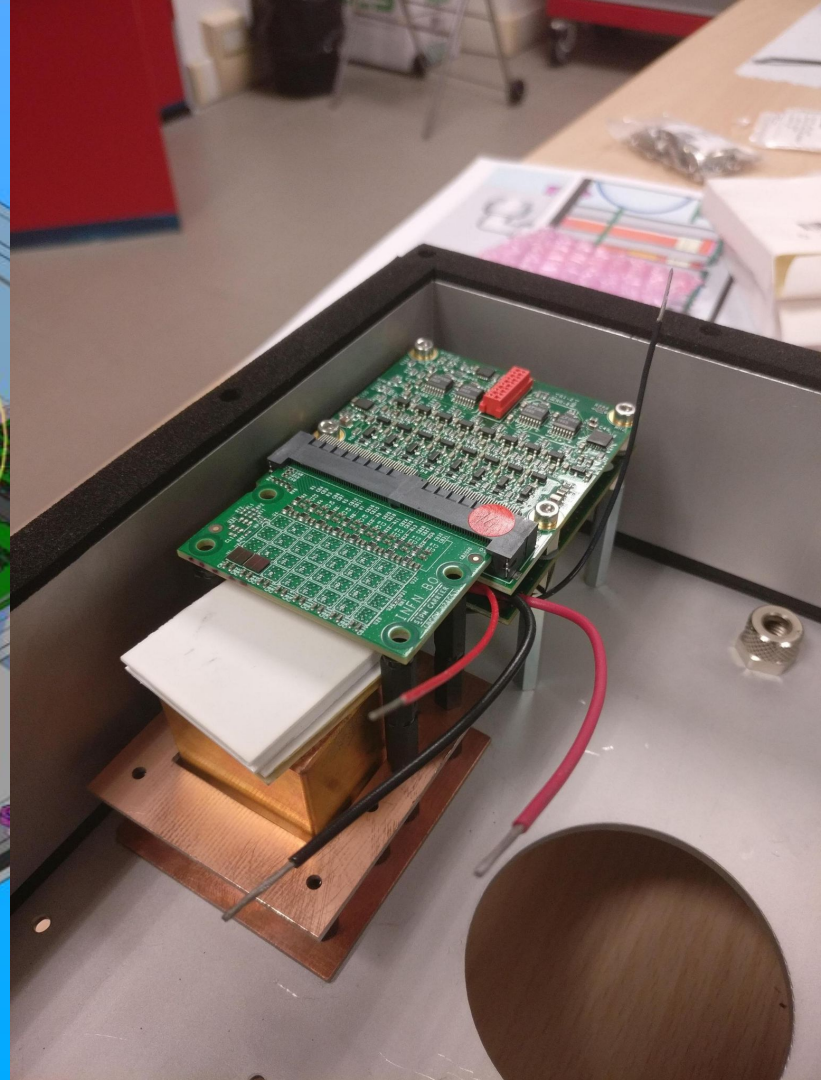


CAD drawings are taking shape towards SPS tests beam this month





thanks to all the people who worked hard to come till so far !!!



qualche slide extra sulle attività / richieste 2022

in sinergia con ALICE 3 RICH

Matrici proto-readout-tile RICH (SiPM FBK)

CORPO DEL DOCUMENTO														
Linea	Cod.	Tipo C/P	Descrizione	Q.ta	Val. Unit.	Scont / Magg.	Val.Tot.	IVA (%)	Ritenuta	Natura	Dal	Al	Rif. Amm.	Altro
1			FBK SiPM mini-tiles 4x2 Ordine di acquisto n. 6166 del 03-DIC-20 CIG: Z4C2ECD620	3.00UN	470.00		1410.00	22.00						

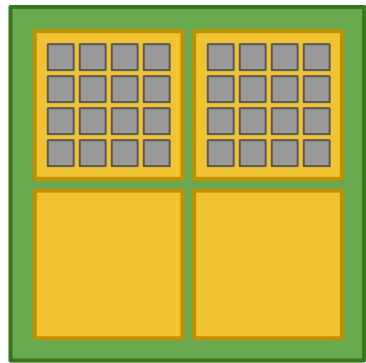
ordine nel 2020 acquisto sensori SiPM FBK: tile 4x2, costo unitario 0.5 kEUR
previsione per tile 4x4, costo unitario 1 k EUR

preventivo per sviluppo in collaborazione con FBK di unità proto-readout-tile per radiazione Cherenkov: dettagli specifici da definire, contatto con FBK iniziato per discussione interesse e possibili soluzioni

stima costi proto-readout-tile composta di 4 mini-tiles SiPM FBK 4x4
realizzazione di 4 unità proto-readout-tile, non complete (2 mini-tile + 2 dummy)

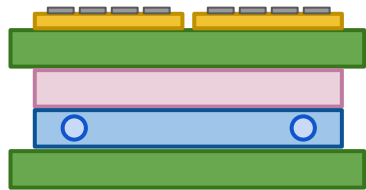
- 8x mini-tiles SiPM FBK 4x4 = 8 kEUR
- 4x celle Peltier = 0.5 kEUR
- water-cooling = officina meccanica
- extra costi (connettori, assemblaggio, ...) = 1.5 kEUR

TOTALE richiesto = 10 kEUR (consumo)



30 mm

proto-readout-tile
Peltier cell
water-cooling
front-end ASIC



Irraggiamento presso Centro ProtonTerapia (TIFPA)

Con la presente ci preghiamo ordinarvi quanto segue, alle condizioni sottoindicate:

Descrizione sintetica:

QUANTITA'	DESCRIZIONE	SCONTO	%	PREZZO UNITARIO	IMPORTO
1,0	costo fascio protoni per irraggiamento SiPM presso Centro di Protonterapia di Trento il 13 -14-15 Maggio 2021 -- Rilascio documenti di riconsegna come da normativa vigente	0,00	0	2.000,00	2.000,00
ordine 2021 un accesso fascio protoni (2 sere, una mattina, totale 8 ore) = 2.5 EUR					

IVA AL 22% EUR 440,00

TOTALE EUR : 2.000,00
TOTALE EUR (Ivato): 2.440,00

previsti due accessi fascio nel 2022

- 1 accesso per irraggiamento SiPM Broadcom e SENSL = 2.5 k EUR
 - non irraggiati nel 2021 causa rallentamenti dovuti ad attivazione in area controllata
- 1 accesso per seconda fase studi R&D su danni radiazione SiPM = 2.5 kEUR
 - danno da radiazione integrato in diverse fasi nel tempo (come da esperimento)
 - sensore nuovo → irraggiamento → annealing → irraggiamento → annealing

in sinergia con ALICE 3 RICH

TOTALE richiesto = 5 kEUR (consumo)

Schede elettronica per caratterizzazione SiPM

Con la presente ci preghiamo ordinarvi quanto segue, alle condizioni sottoindicate:

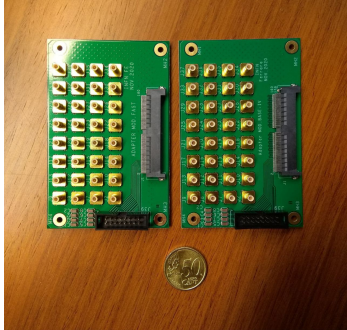
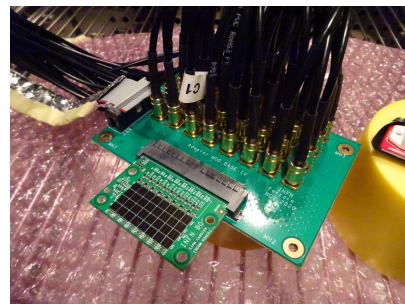
Descrizione sintetica:

QUANTITA'	DESCRIZIONE	SCONTO	%	PREZZO UNITARIO	IMPORTO
1,0	Produzione PCB e assemblaggio schede SiPM Adapter SMB	0,00	0	2.550,00	2.550,00

nel 2021 schede adapter SMB per caratterizzazione IV SiPM = 3.0 kEUR
di cui connettori SMB forniti in conto/lavorazione = 1.0 kEUR
e corrispondenti cavi e adattatori per effettuare misure = 1.0 kEUR

IVA AL 22% EUR 561,00

TOTALE EUR : 2.550,00
TOTALE EUR (Ivato): 3.111,00



supportare necessità sviluppo schede per continuamento attività R&D e caratterizzazione SiPM, di cui i dettagli non ancora ancora sviluppati

- break-out / adapter board ottimizzata per PDE e SPTR
- break-out / adapter board per interfaccia con multiplexer (automatizzazione misure caratterizzazione)

più necessità supporto metabolismo R&D, acquisto componenti, cavi
più supporto necessità specifiche all'attività sinergica per il RICH di ALICE 3

in sinergia con ALICE 3 RICH

TOTALE richiesto = 5 kEUR (consumo) + 5 kEUR sj. (sottomissione Lol ALICE 3)

Evoluzione ALCOR++ chip ottimizzato per RICH

ALCOR:

- Developed by INFN Torino originally for a Darkside application
- Optimized for cryo operation
- An ALCOR++ optimised for RICH application will be next step

The microelectronics group at TO will design a second version of ALCOR featuring:

- bug fixes to the pixel control logic, problems observed during experimental characterisation and post-layout simulations occur when the TDCs operate at very high data rate
- a new and optimised very front-end, implementing a pole-zero cancellation circuit, suitable for the readout of SiPMs with high DCR

